VRW056 ṂṂȽ SQS ÆṀɥ s Ⅱ ㄱ Silicon PNP transistor in a SOT-23 Plastic Package.

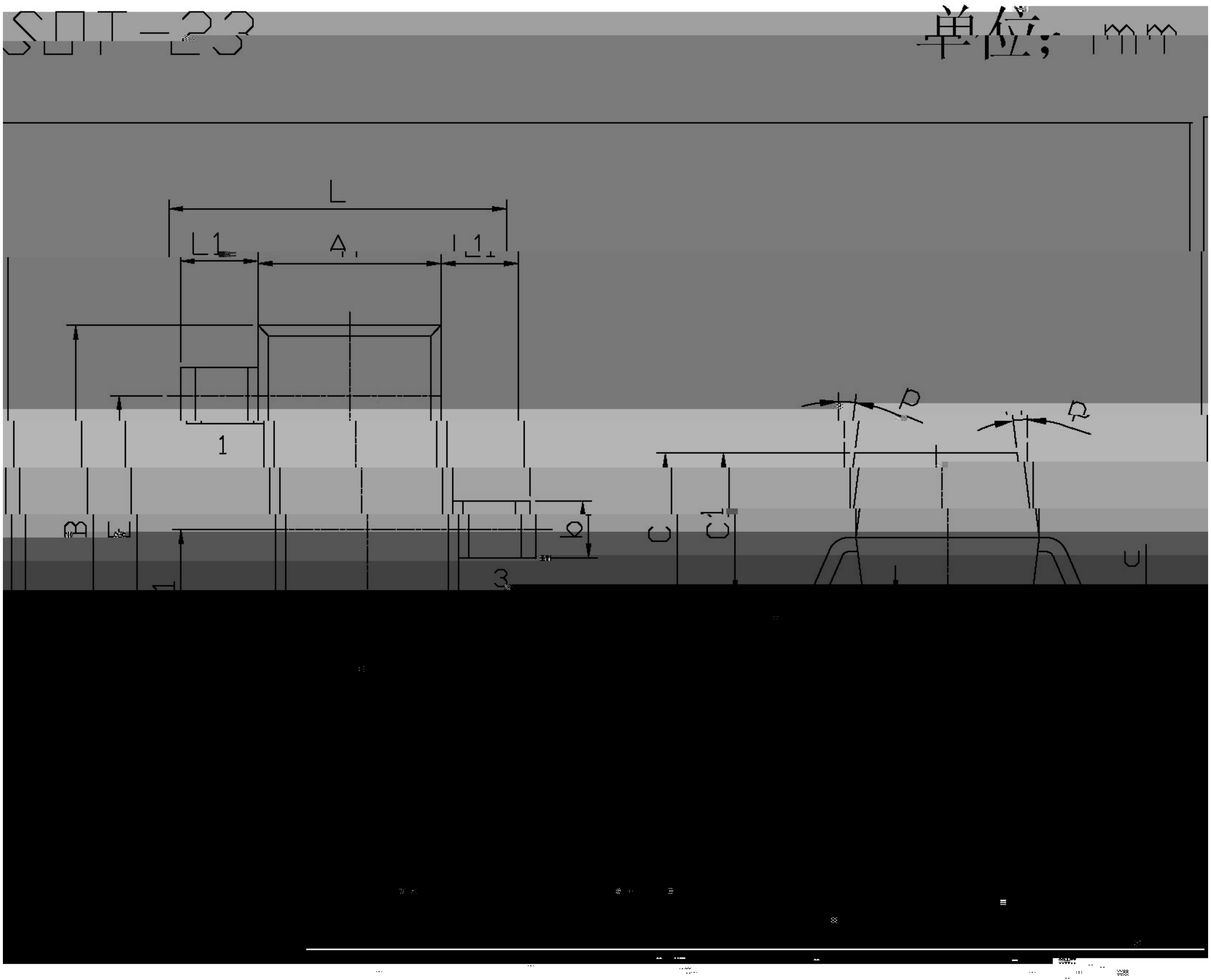
[illegible] $V_{CE(sat)}$
High current gain, Low collector-emitter saturation voltage.

[illegible]
6

| v ΅Ω̦<br>Parameter | ɻ ᴺ<br>Symbol | ΅Ω̦Ӫ<br>Rating | ᴅ Ꞁ<br>Unit |
|---|---|---|---|
| Collector to Base Voltage | $V_{CBO}$ | -50 | V |
| Collector to Emitter Voltage | $V_{CEO}$ | -45 | V |
| Emitter to Base Voltage | $V_{EBO}$ | -5.0 | V |
| Collector Current - Continuous | $I_C$ | -100 | mA |
| Collector Power Dissipation | $P_C$ | 350 | mW |
| Junction Temperature | $T_j$ | 150 | |
| Storage Temperature Range | $T_{stg}$ | -55 150 | |

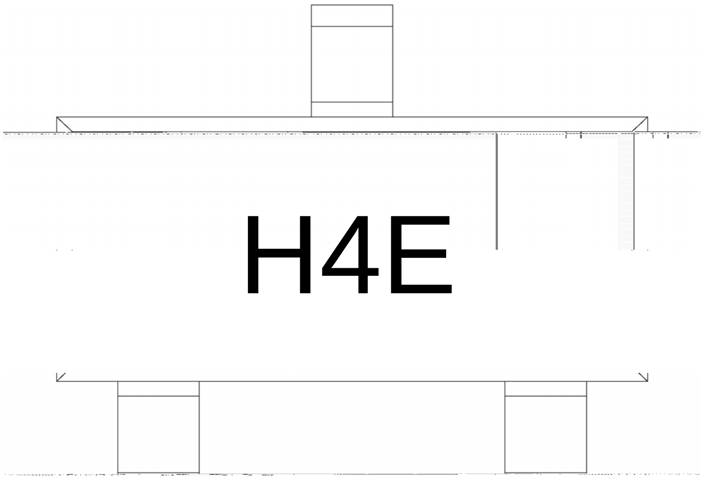
| v ΅Ω̦<br>Parameter | ɻ ᴺ<br>Symbol | ╝ ⁏ᛏ ʈ<br>Test Conditions | ῳ ṇ Ӫ<br>Min | Ɛ ʓ Ӫ<br>Typ | ῳ ⸗ Ӫ<br>Max | ᴅ Ꞁ<br>Unit |
|---|---|---|---|---|---|---|
| Collector to Emitter Breakdown Voltage | $V_{CEO}$ | $I_C$=-10mA $I_B$=0 | -45 | | | V |
| Collector to Base Breakdown Voltage | $V_{CBO}$ | $I_C$C I | E | | O | |

## / Package Dimensions



| | | | | |
|---|---|---|---|---|
| E | 1.70 | 2.10 | M | 0.20MIN. |
| E1 | 0.85 | 1.05 | P | 7° |
| b | 0.35 | 0.55 | | |

## / Marking Instructions



ب ˝ χ

K χ Ѭ ʒ ᴎ Ⴇ

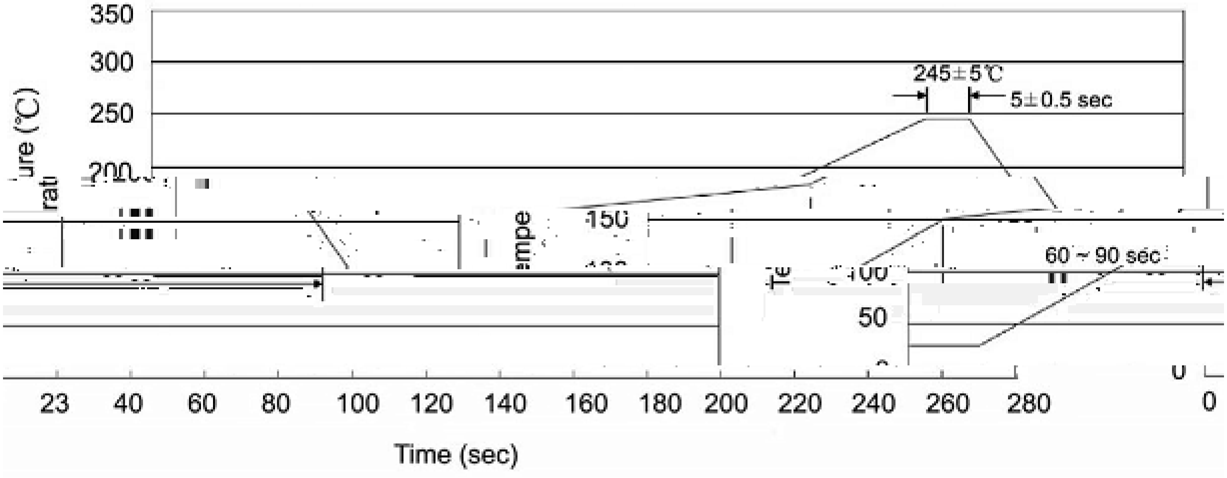
7H χ Ѭ ʒ ᴺ Ⴇ

Note:

H: Company Code.

4E: Product Type Code

## (　　) / Temperature Profile for IR Reflow Soldering(Pb-Free)



ب ˝ χ

1 ỉ ♬ □ ẙ 25 Ḱ 150 ɫ ı `H ڗ 60 Ḱ 90sec;

2 Ś Ӫ □ ẙ 245 ° 5 ɫ ı `H ڗ ʽY ʎ ʭ 5 ° 0.5sec;

3 ì ˙ ˥ ˛ ɔ ﻬ ẙ ʭ 2 Ḱ 10 ɫ /sec.

Note:

1.Preheating:25~150 ɫ , Time:60~90sec.

2.Peak Temp.:245 ° 5 ɫ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɫ /sec.

## / Resistance to Soldering Heat Test Conditions

□ ẙ χ 260±5　　`H ڗ χ 10±1 sec.

Temp.:260±5　　Time:10±1 sec

## / Packaging SPEC.

ດ` ɣ ե / REEL

| Package Type | Units | | | | | Dimension | | (unit mm$^3$) |
|---|---|---|---|---|---|---|---|---|
| | Units/Reel / | Reels/Inner Box / | Units/Inner Box / | Inner Boxes/Outer Box / | Units/Outer Box / | Reel | Inner Box | Outer Box |
| SOT-23 | 3,000 | 10 | 30,000 | 6 | 180,000 | 7 ×8 | 180×120×180 | 390×385×205 |

## / Notices